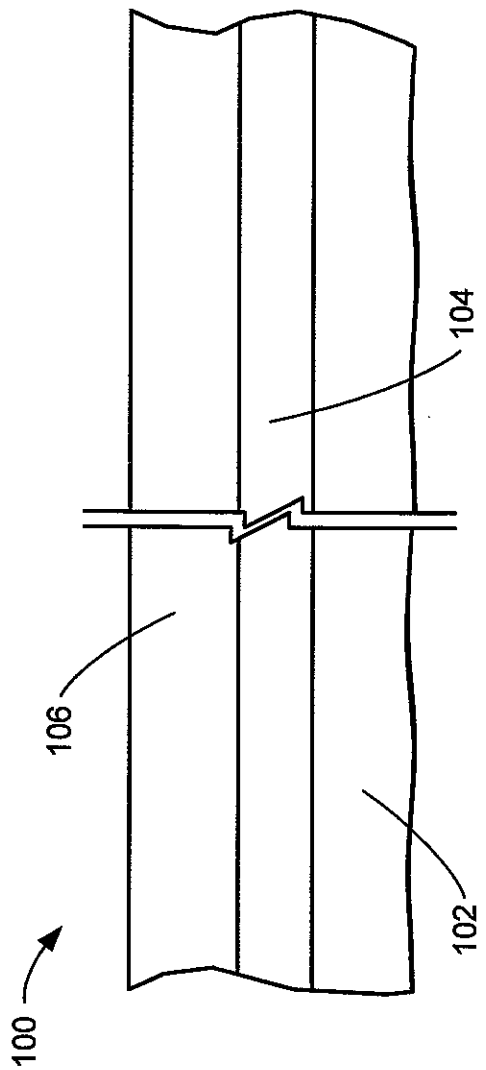


FIG. 1

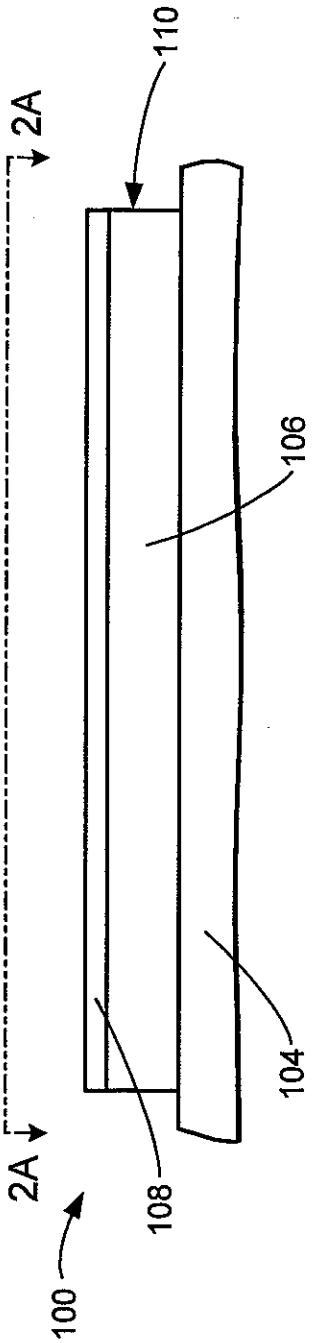


FIG. 2

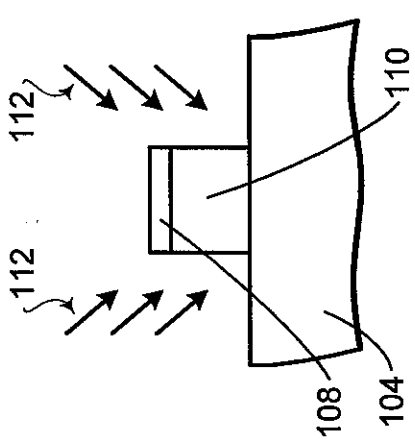


FIG. 2B

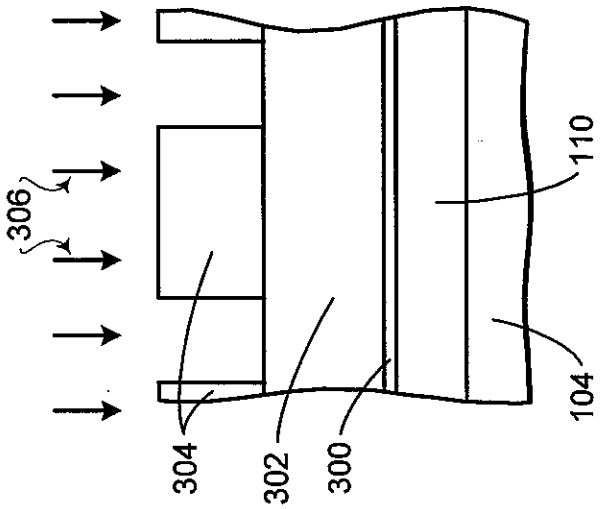


FIG. 3

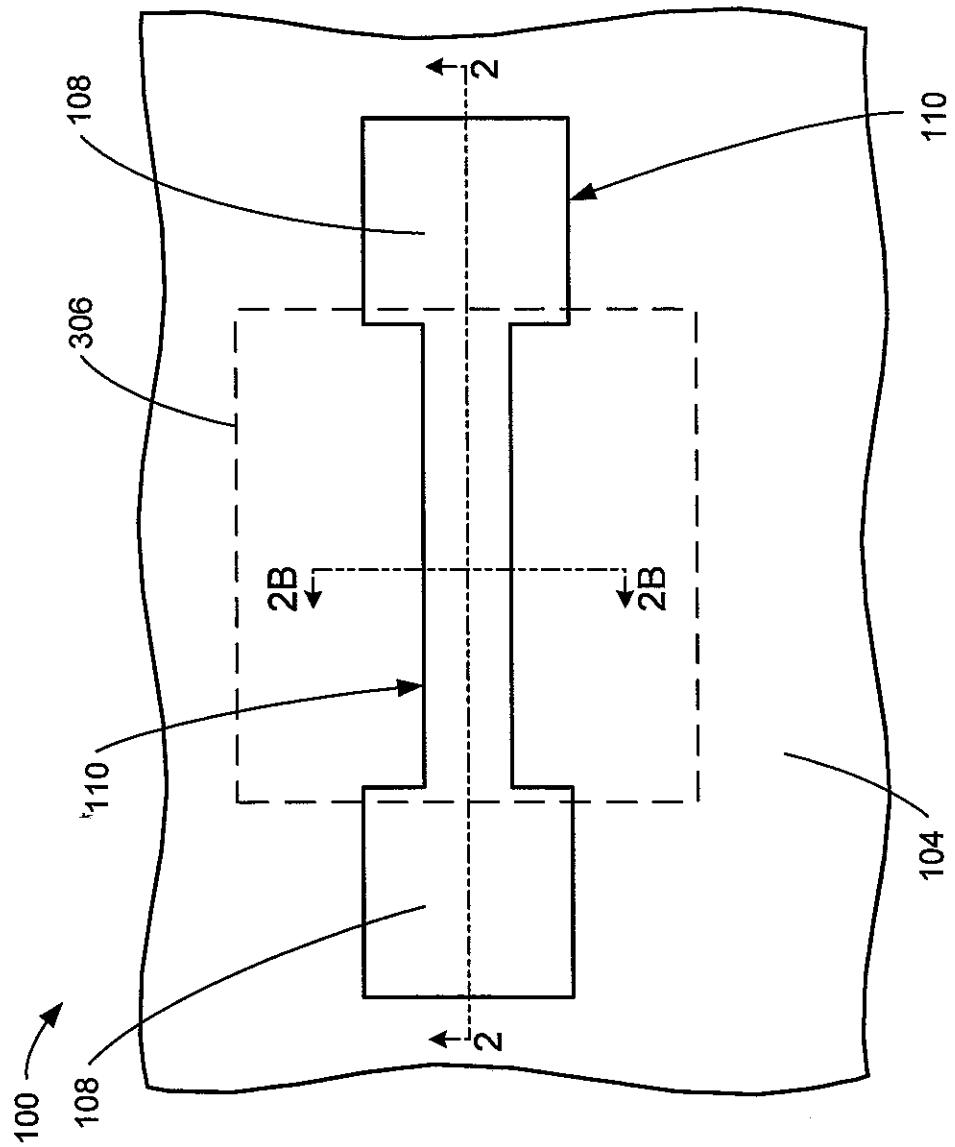


FIG. 2A

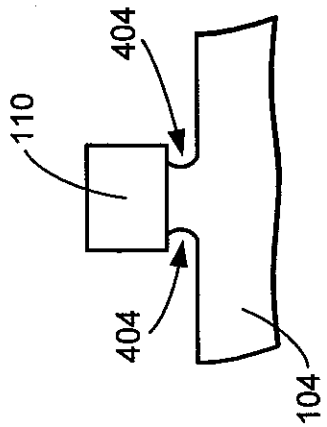


FIG. 4A

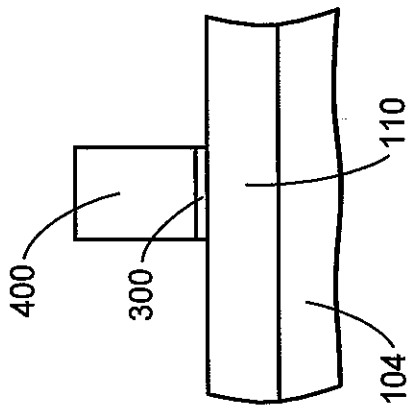


FIG. 4B

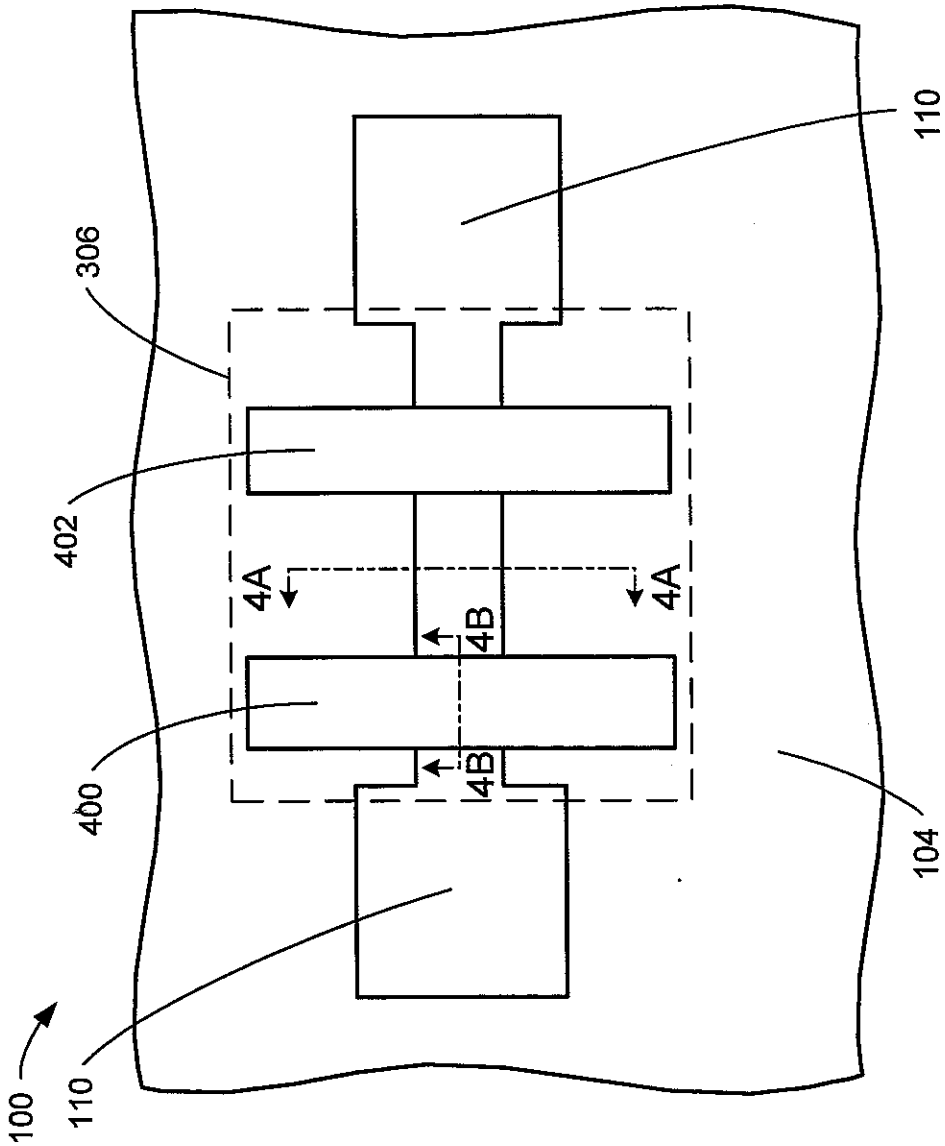


FIG. 4

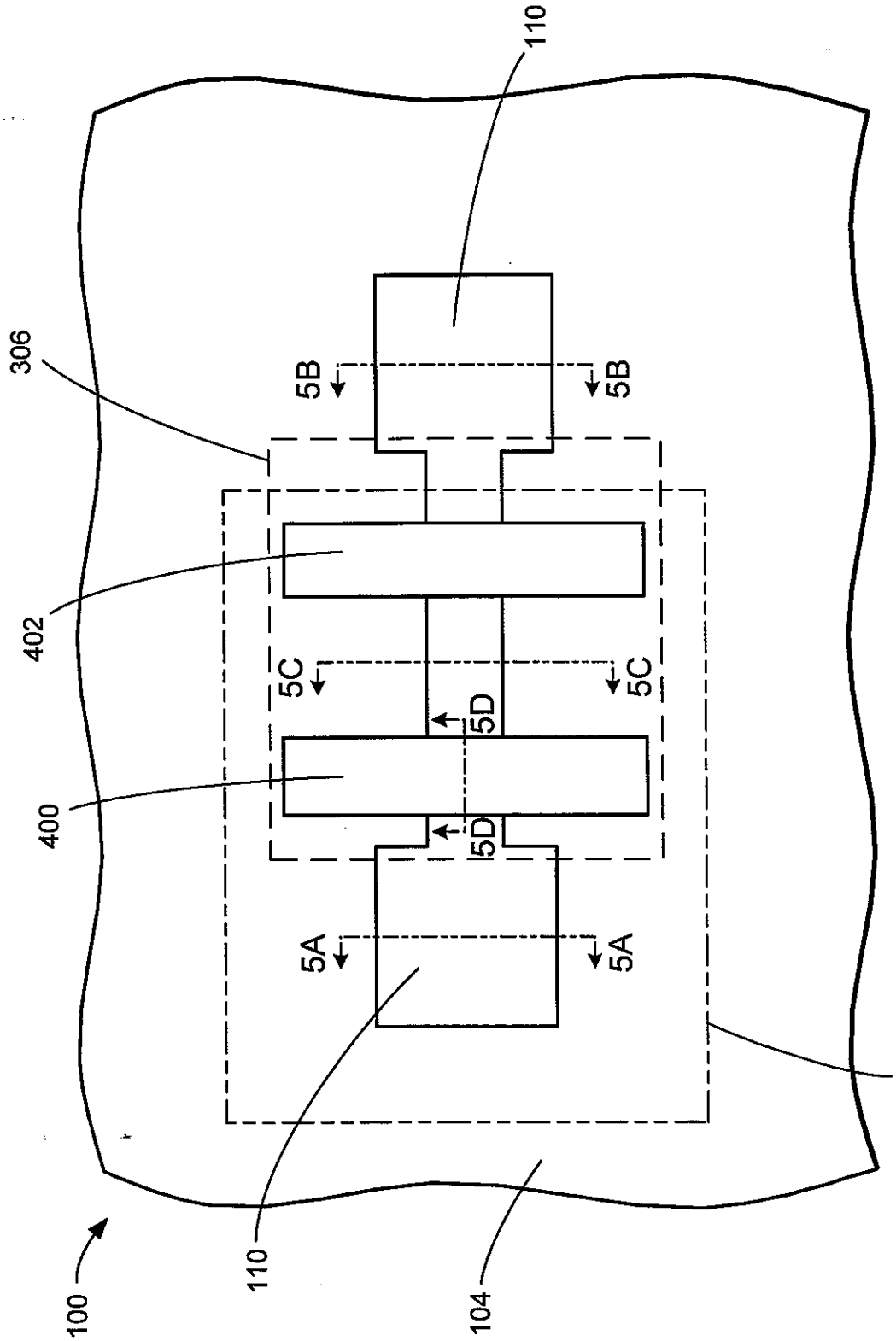


FIG. 5

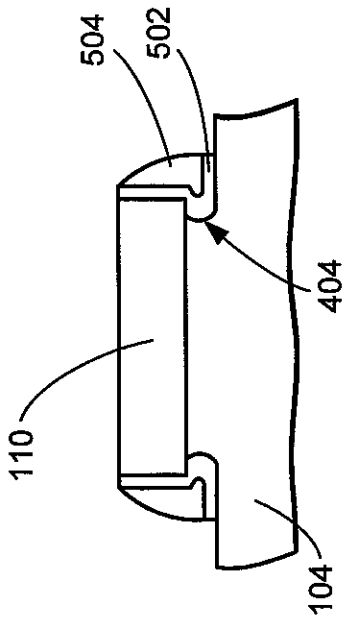


FIG. 5B

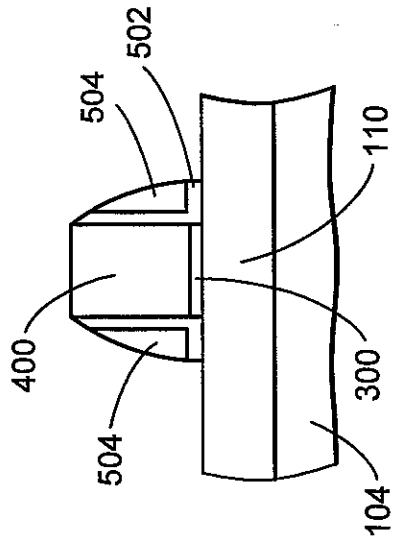


FIG. 5D

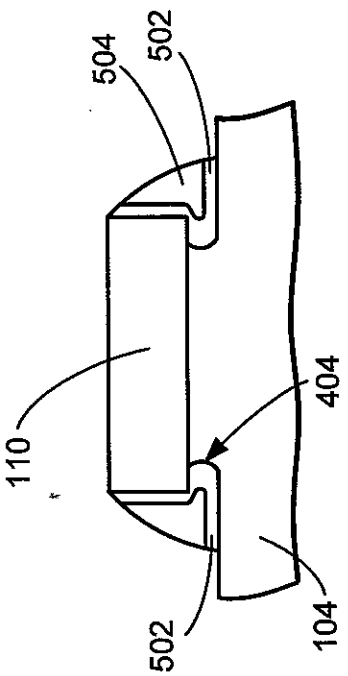


FIG. 5A

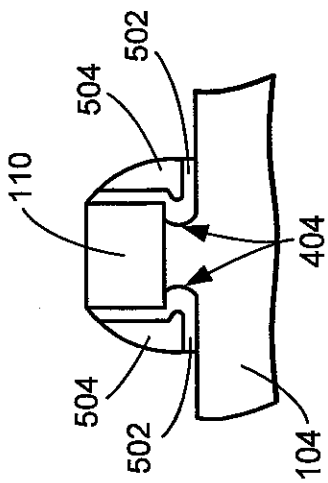


FIG. 5C

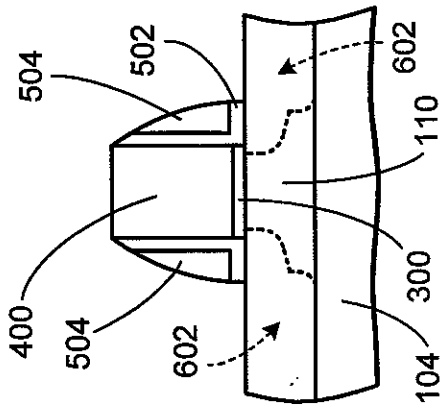

504
502
602
110
300
400
504
602
104

FIG. 6A

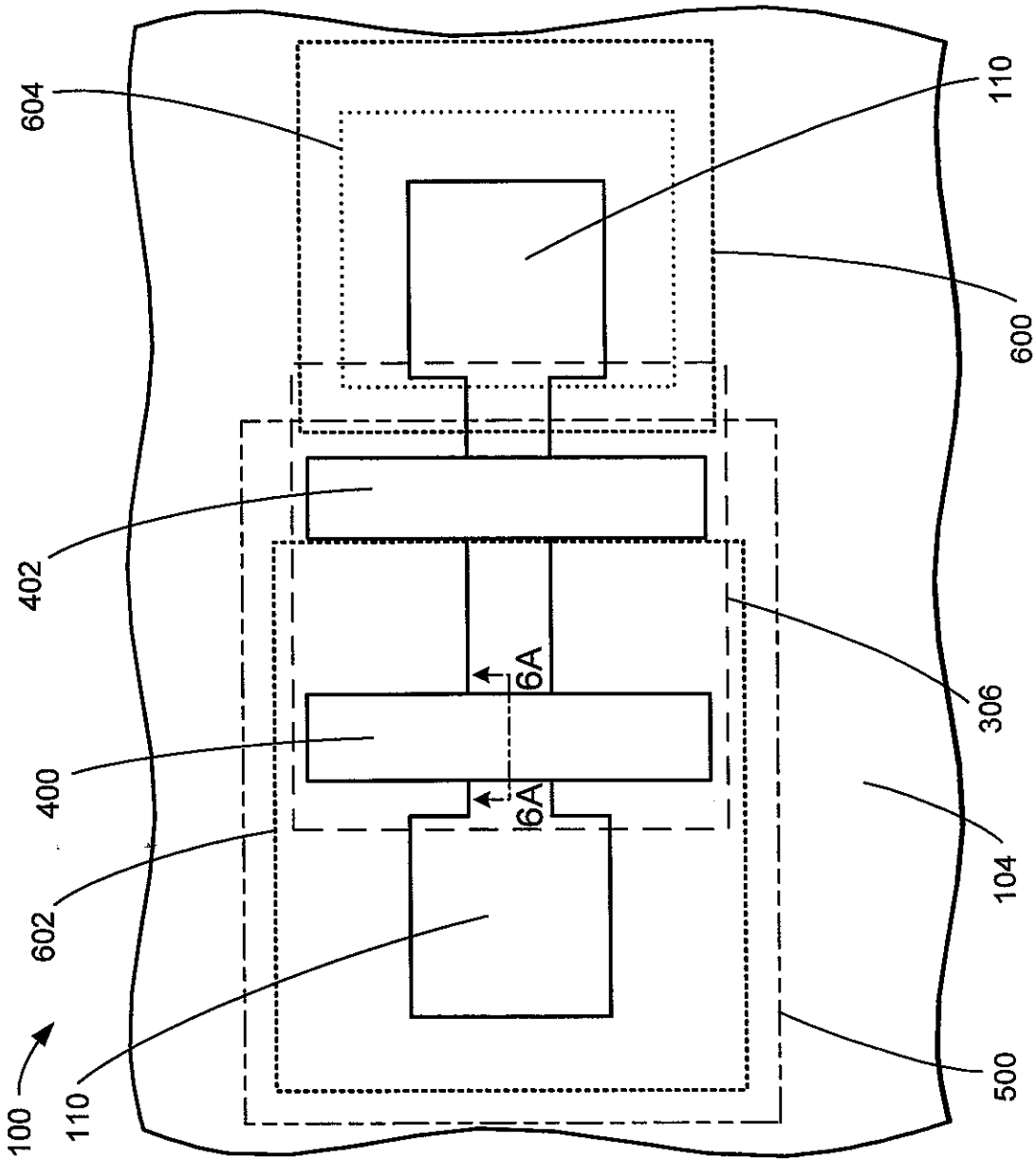

604
110
600
402
6A
306
400
6A
602
104
100
110
500

FIG. 6

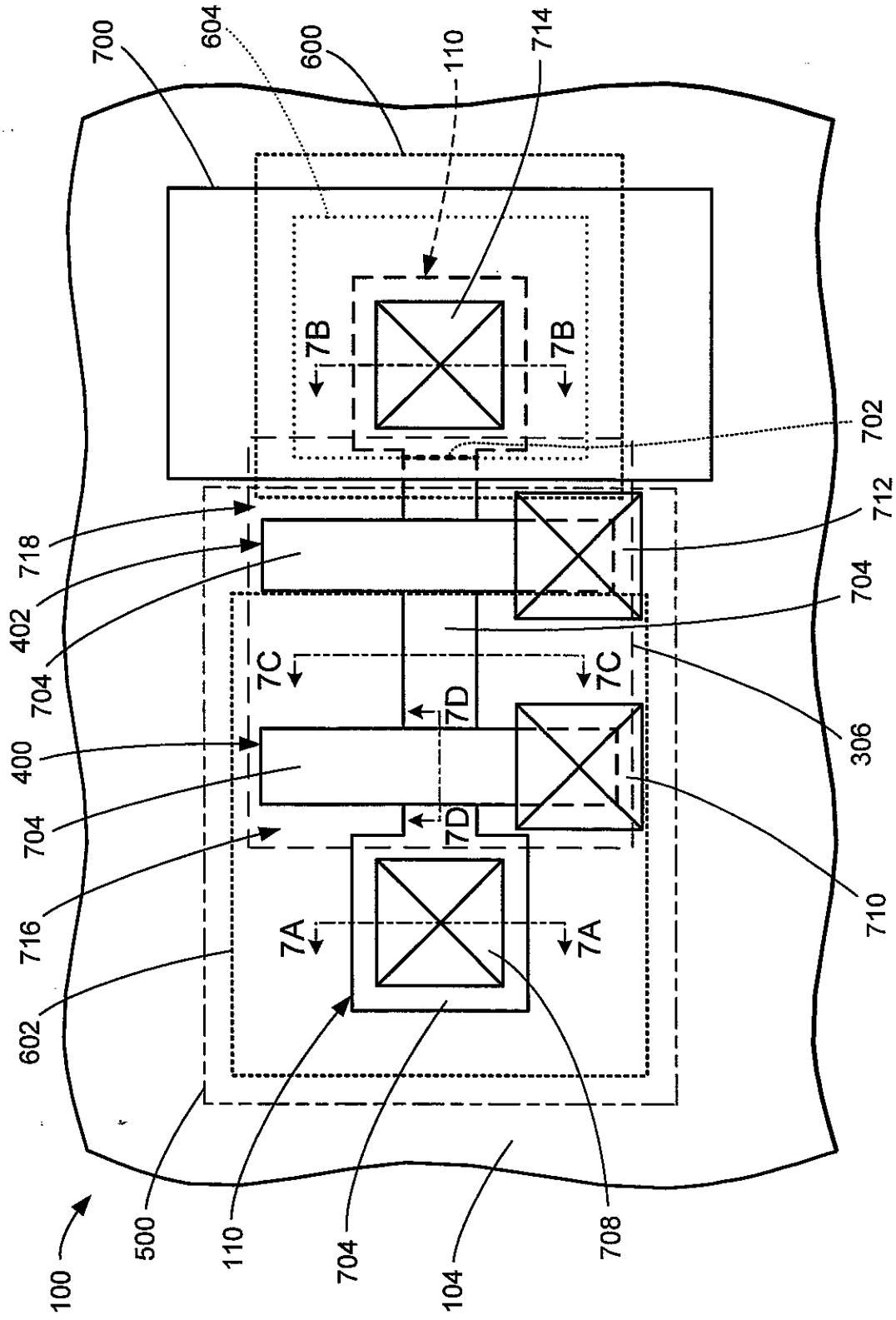

700
604
600
110
714
7B
7B
702
718
712
402
704
704
7C
7C
7D
306
400
704
7D
716
710
7A
7A
602
500
110
704
104
708
100

FIG. 7

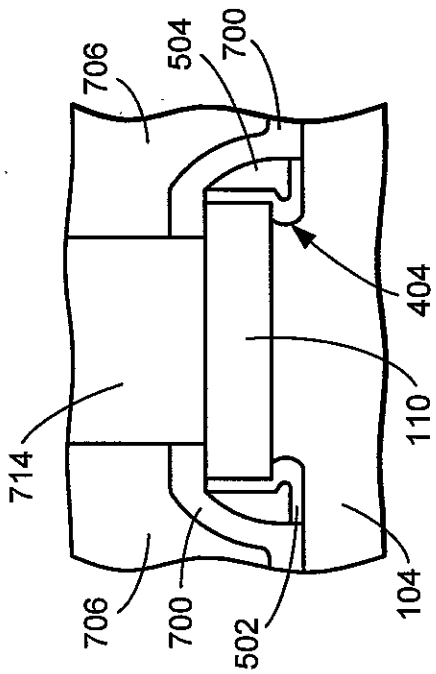


FIG. 7B

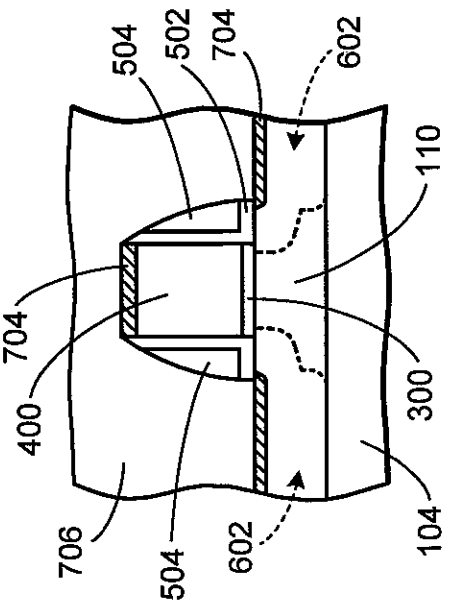


FIG. 7D

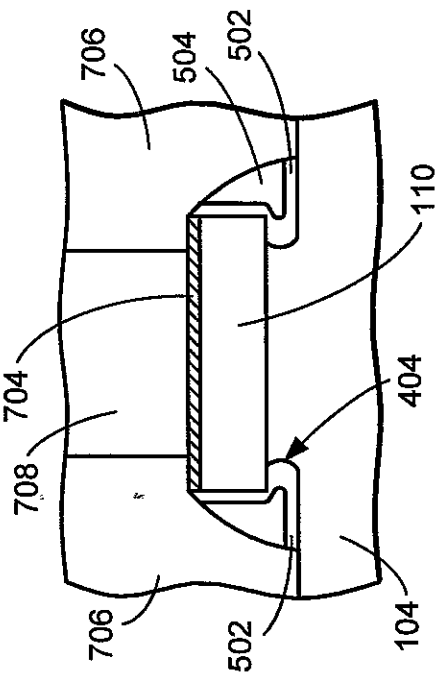


FIG. 7A

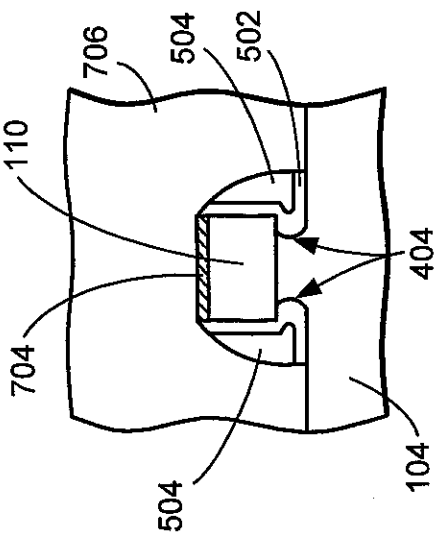


FIG. 7C

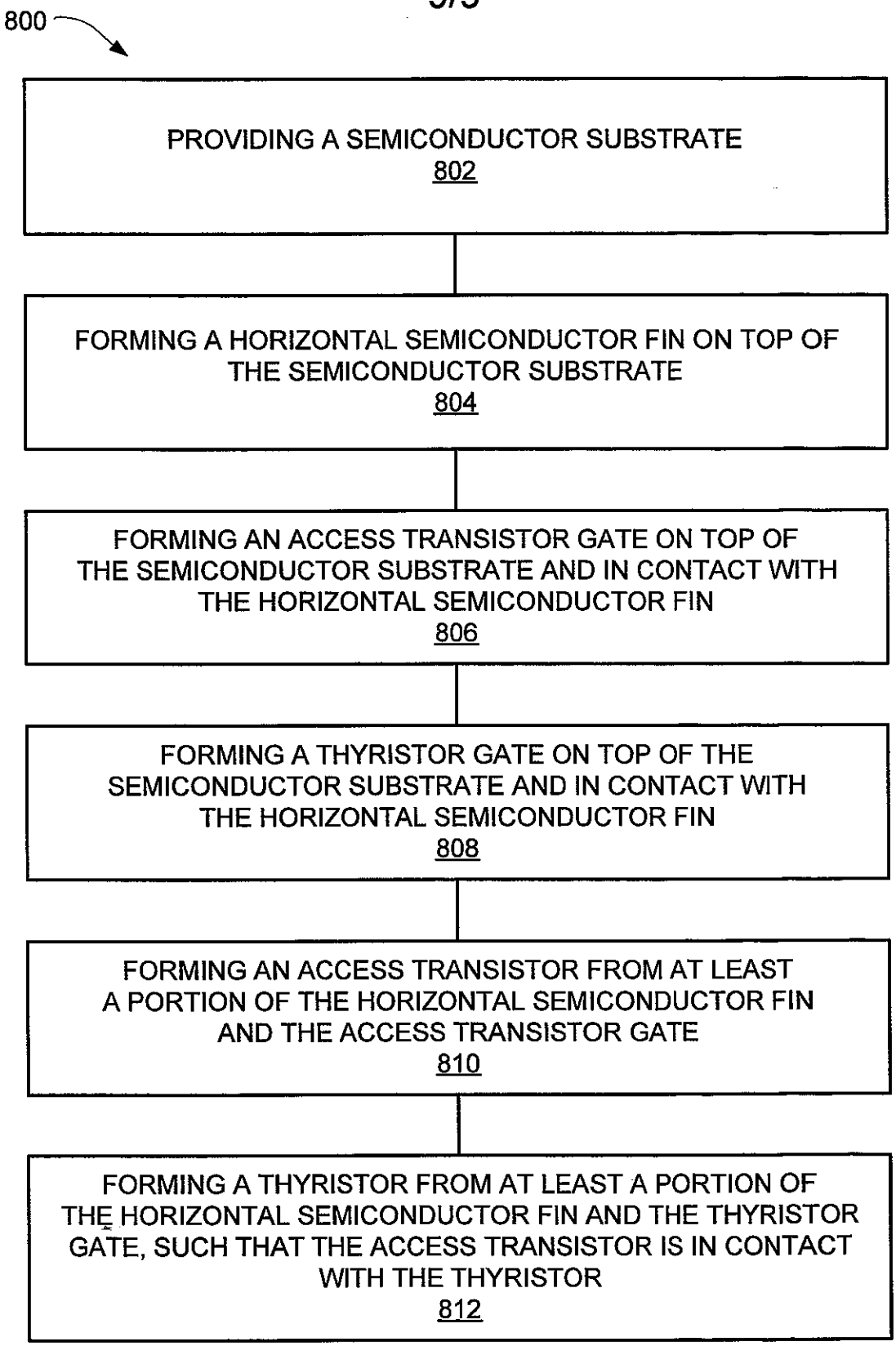

800
PROVIDING A SEMICONDUCTOR SUBSTRATE
802
FORMING A HORIZONTAL SEMICONDUCTOR FIN ON TOP OF THE SEMICONDUCTOR SUBSTRATE
804
FORMING AN ACCESS TRANSISTOR GATE ON TOP OF THE SEMICONDUCTOR SUBSTRATE AND IN CONTACT WITH THE HORIZONTAL SEMICONDUCTOR FIN
806
FORMING A THYRISTOR GATE ON TOP OF THE SEMICONDUCTOR SUBSTRATE AND IN CONTACT WITH THE HORIZONTAL SEMICONDUCTOR FIN
808
FORMING AN ACCESS TRANSISTOR FROM AT LEAST A PORTION OF THE HORIZONTAL SEMICONDUCTOR FIN AND THE ACCESS TRANSISTOR GATE
810
FORMING A THYRISTOR FROM AT LEAST A PORTION OF THE HORIZONTAL SEMICONDUCTOR FIN AND THE THYRISTOR GATE, SUCH THAT THE ACCESS TRANSISTOR IS IN CONTACT WITH THE THYRISTOR
812

FIG. 8